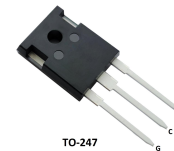
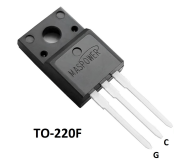
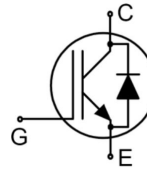


Features

- Low gate charge
- Trench FS Technology
- Fast switching speed
- Low switching losses

Applications

- PFC
- UPS
- Inverter
- Welding Machine



Absolute Maximum Ratings

Parameter		Symbol	Value	Unit
Collector-emitter voltage		V_{CES}	650	V
Gate-emitter voltage		V_{GES}	± 30	
Collector current*	$T_C = 25^\circ\text{C}$	I_C	60	A
	$T_C = 100^\circ\text{C}$		30	
Pulsed collector current, pulse time limited by T_{jmax} (note1)		I_{CM}	120	
Diode forward current	$T_C = 25^\circ\text{C}$	I_F	60	
	$T_C = 100^\circ\text{C}$		30	
Diode pulsed current, Pulse time limited by T_{jmax}		I_{FM}	120	
Power dissipation(TO-220F)		P_D	35	W
Power dissipation(TO-247/TO-220)		P_D	230	W
Operating Junction and storage temperature rang(note2)		T_J	-55 to 175	$^\circ\text{C}$
		T_{stg}	-55 to 175	

Electrical Characteristics ($T_C = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static Characteristics						
Collector-emitter breakdown voltage	BV_{CES}	$I_C = 500\mu\text{A}$, $V_{GE} = 0\text{V}$	650	-	-	V
Gate-emitter threshold voltage	$V_{GE(th)}$	$V_{CE} = V_{GE}$, $I_C = 250\mu\text{A}$	3.5	4.5	5.5	
Zero gate voltage collector current	I_{CES}	$V_{CE} = 650\text{V}$, $V_{GE} = 0\text{V}$	-	-	50	μA
Gate-emitter leakage current	I_{GES}	$V_{GE} = 20\text{V}$, $V_{CE} = 0\text{V}$	-	-	± 200	nA
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 30\text{A}$, $V_{GE} = 15\text{V}$, $T_C = 25^\circ\text{C}$	-	1.7	-	V
Dynamic and Switching Characteristics						
Total gate charge	Q_g	$V_{CE} = 520\text{V}$, $I_C = 30\text{A}$,	-	62	-	nC

Gate emitter charge	Q _{ge}	V _{GE} = 15V	-	9.5	-	nC
Gate Collector Charge	Q _{gc}		-	33	-	nC
Input capacitance	C _{ies}	V _{CE} = 25V, V _{GE} = 0V, f = 1MHz	-	955	-	pF
Reverse transfer capacitance	C _{res}		-	107	-	
Output capacitance	C _{oes}		-	33	-	
Turn-on delay time	t _{d(on)}	V _{GE} = 15V, V _{CC} = 400V, I _C = 30A, R _G = 10Ω, Inductive Load, T _C = 25°C	-	11	-	nS
Rise time	t _r		-	42	-	
Turn-off delay time	t _{d(off)}		-	89	-	
Fall time	t _f		-	73	-	
Turn-on switching energy	E _{on}		-	0.53	-	mJ
Turn-off switching energy	E _{off}		-	0.55	-	
Total switching energy	E _{ts}		-	1.0	-	
Turn-on delay time	t _{d(on)}	V _{GE} = 15V, V _{CC} = 400V, I _C = 30A, R _G = 10Ω, Inductive Load, T _C = 150°C	-	10	-	nS
Rise time	t _r		-	44	-	
Turn-off delay time	t _{d(off)}		-	114	-	
Fall time	t _f		-	130	-	
Turn-on switching energy	E _{on}		-	0.52	-	mJ
Turn-off switching energy	E _{off}		-	0.79	-	
Total switching energy	E _{ts}		-	1.30	-	
Diode Characteristics (T _c =25°C unless otherwise specified)						
Forward voltage	V _F	I _F =30A,T _C =25°C	-	1.4	-	V
Reverse recovery time	t _{rr}	I _F =30A,di/dt=200A/μS T _C =25°C	-	50	-	nS
Reverse recovery current	I _{rr}		-	2.5	-	A
Reverse recovery charge	Q _{rr}		-	0.31	-	uC

Thermal Characteristics

Parameter	Symbol	Max.		Unit
		TO-220F	TO-220 TO-247	
Thermal resistance junction-to-case for IGBT	R _{θJC}	3.57	0.65	°C/W
Thermal resistance junction-to-case for Diode	R _{θJC}	7.7	40	
Thermal resistance junction-to-ambient	R _{θJA}	62.5		

*Collector current limited by maximum junction temperature.

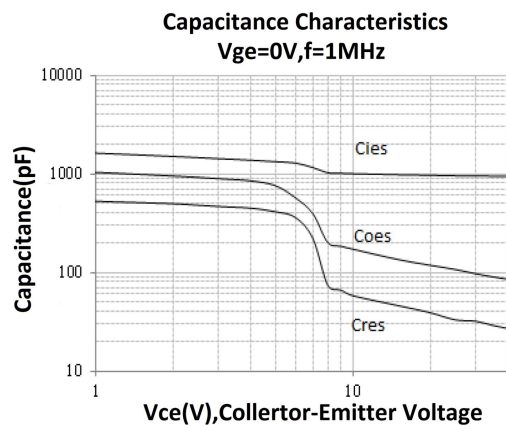
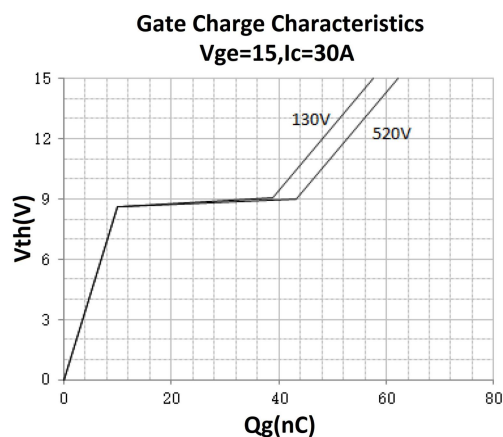
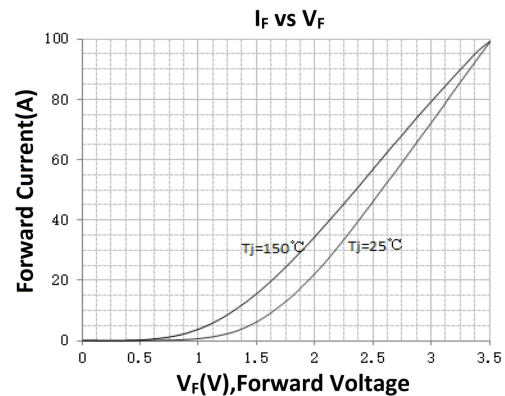
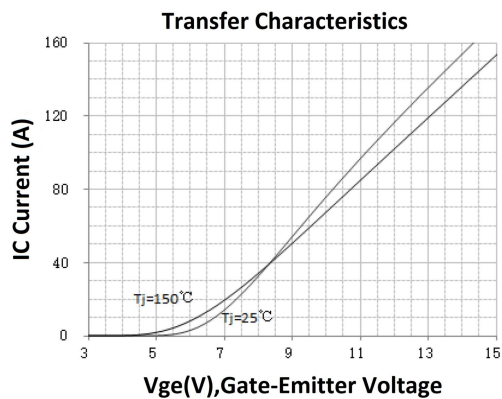
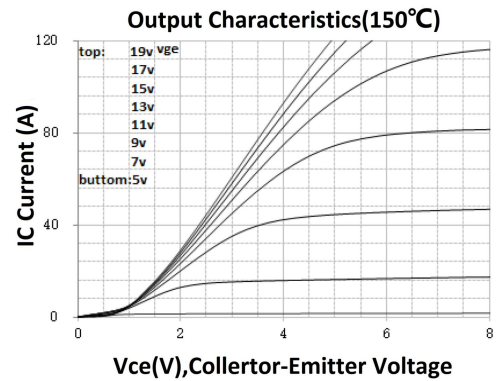
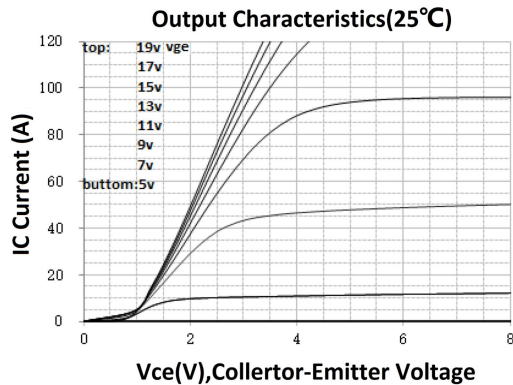
1: Pulse width limited by maximum junction temperature.

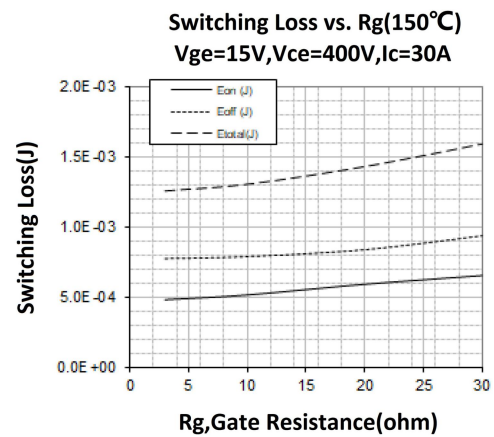
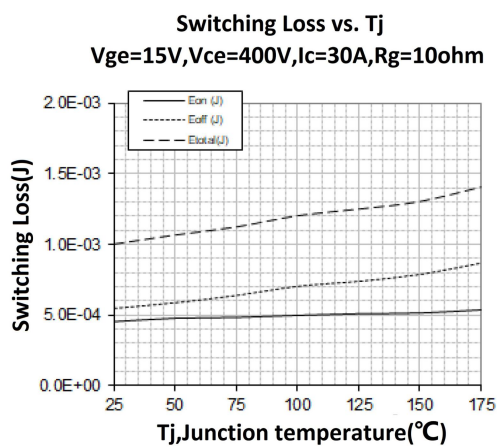
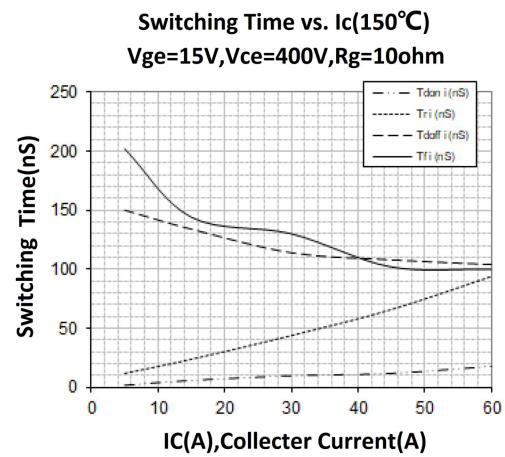
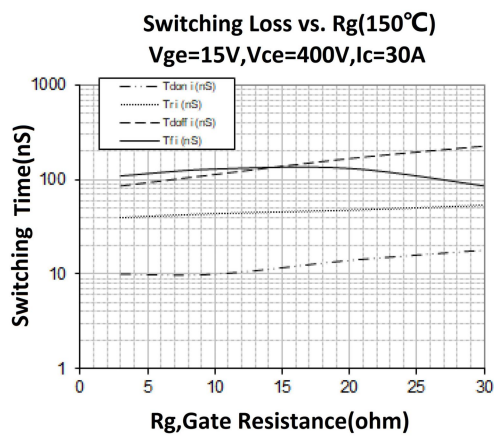
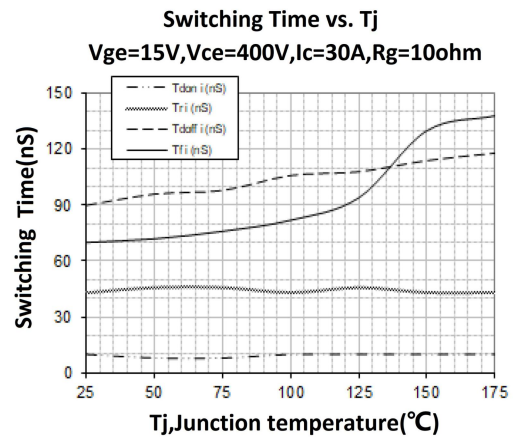
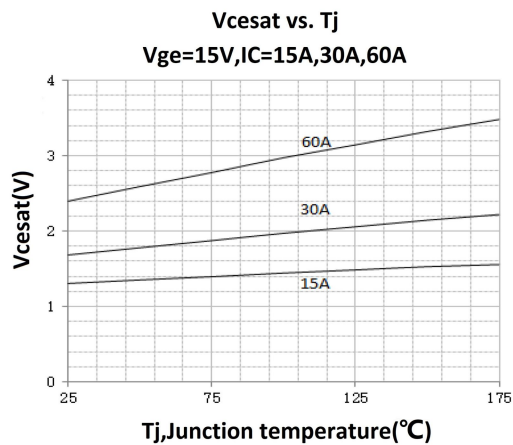
2: Under overload condition, it is allowed to operate at the maximum junction temperature T_{vjop} = 175 °C, and the maximum duty ratio is less than 20% (lasting for 60 s at most)

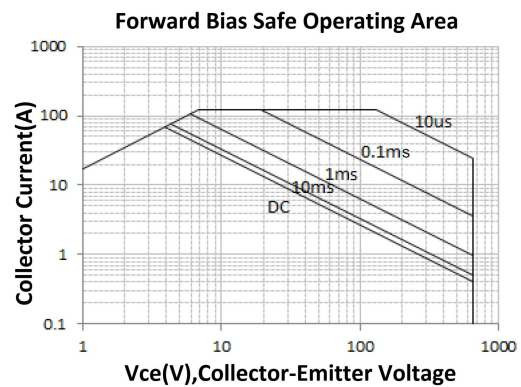
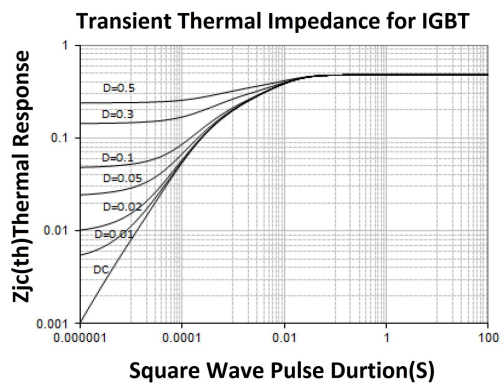
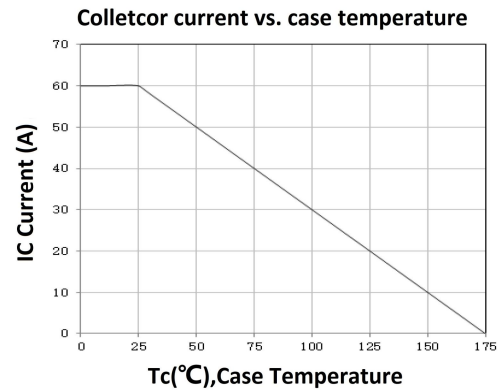
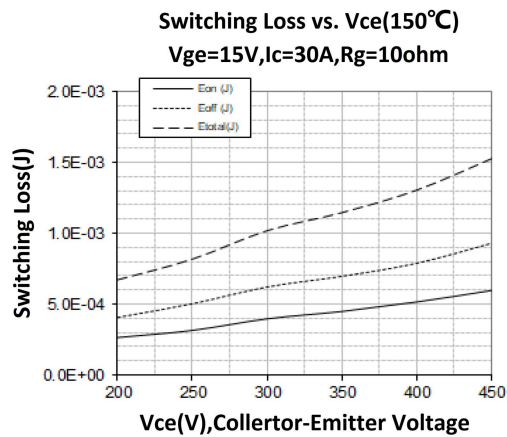
Order Message

Order codes	Package	Packaging
MSG30T65HHT1	TO-220F	Tube
MSG30T65HHC0	TO-247	Tube
MSG30T65HHT0	TO-220	Tube

Typical Performance Characteristic







Package outline dimension

